

High Voltage NPN Silicon Power Transistors

TIP47G, TIP48G, TIP50G

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

Features

- Popular TO-220 Plastic Package
- Complementary to the MJE5730 and MJE5731 Series
- These Devices are Pb-Free and are RoHS Compliant*

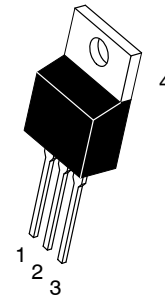
MAXIMUM RATINGS

Symbol	Rating	TIP47	TIP48	TIP50	Unit
V_{CEO}	Collector – Emitter Voltage	250	300	400	Vdc
V_{CB}	Collector – Base Voltage	350	400	500	Vdc
V_{EB}	Emitter – Base Voltage	5.0			Vdc
I_C	Collector Current – Continuous	1.0			Adc
I_{CM}	Collector Current – Peak	2.0			Adc
I_B	Base Current	0.6			Adc
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	40 0.32			W W/ $^\circ\text{C}$
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	2.0 0.016			W W/ $^\circ\text{C}$
E	Unclamped Inducting Load Energy (See Figure 8)	20			mJ
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-65 to +150			$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

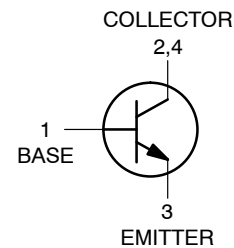
THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3.125	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

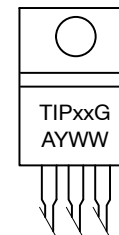


TO-220AB
CASE 221A
STYLE 1

1.0 AMPERE POWER TRANSISTORS NPN SILICON 250–300–400 VOLTS 40 WATTS



MARKING DIAGRAM



TIPxx = Device Code
 xx = 47, 48, or 50
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

TIP47G, TIP48G, TIP50G

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
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OFF CHARACTERISTICS

$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 30\text{ mAdc}$, $I_B = 0$)	TIP47 TIP48 TIP50	250 300 400	– – –	Vdc
I_{CEO}	Collector Cutoff Current ($V_{CE} = 150\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 200\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 300\text{ Vdc}$, $I_B = 0$)	TIP47 TIP48 TIP50	– – –	1.0 1.0 1.0	mAdc
I_{CES}	Collector Cutoff Current ($V_{CE} = 350\text{ Vdc}$, $V_{BE} = 0$) ($V_{CE} = 400\text{ Vdc}$, $V_{BE} = 0$) ($V_{CE} = 500\text{ Vdc}$, $V_{BE} = 0$)	TIP47 TIP48 TIP50	– – –	1.0 1.0 1.0	mAdc
I_{EBO}	Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		–	1.0	mAdc

ON CHARACTERISTICS (Note 1)

h_{FE}	DC Current Gain ($I_C = 0.3\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$)	30 10	150 –	–
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = 1.0\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	–	1.0	Vdc
$V_{BE(on)}$	Base-Emitter On Voltage ($I_C = 1.0\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$)	–	1.5	Vdc

DYNAMIC CHARACTERISTICS

f_T	Current-Gain – Bandwidth Product ($I_C = 0.1\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 2.0\text{ MHz}$)	10	–	MHz
h_{fe}	Small-Signal Current Gain ($I_C = 0.2\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	25	–	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TIP47G, TIP48G, TIP50G

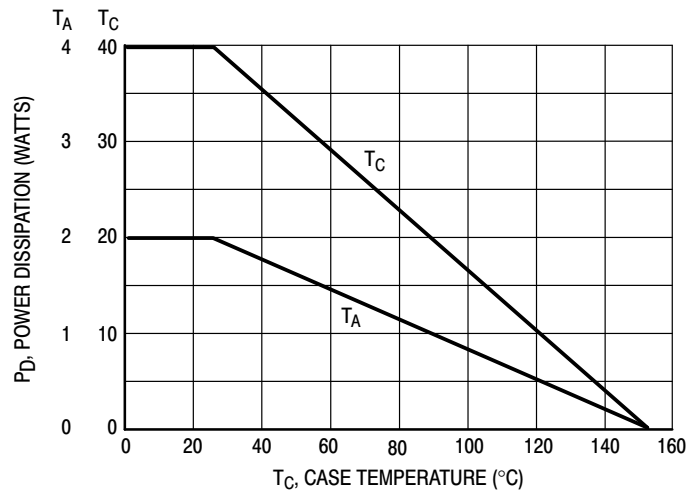
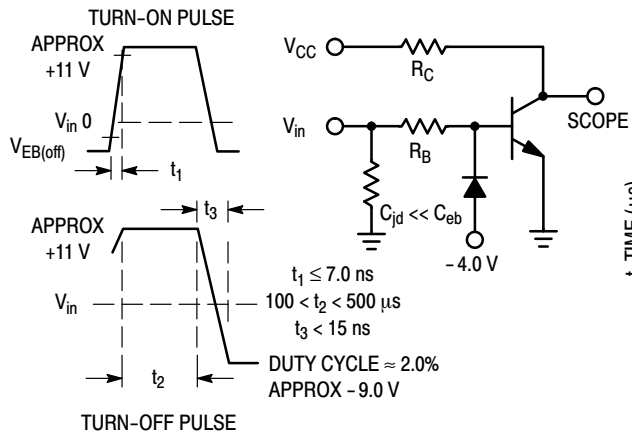


Figure 1. Power Derating



R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS.

Figure 2. Switching Time Equivalent Circuit

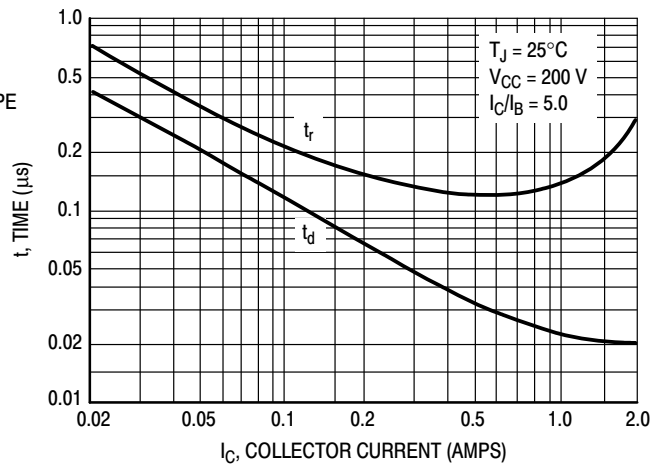


Figure 3. Turn-On Time

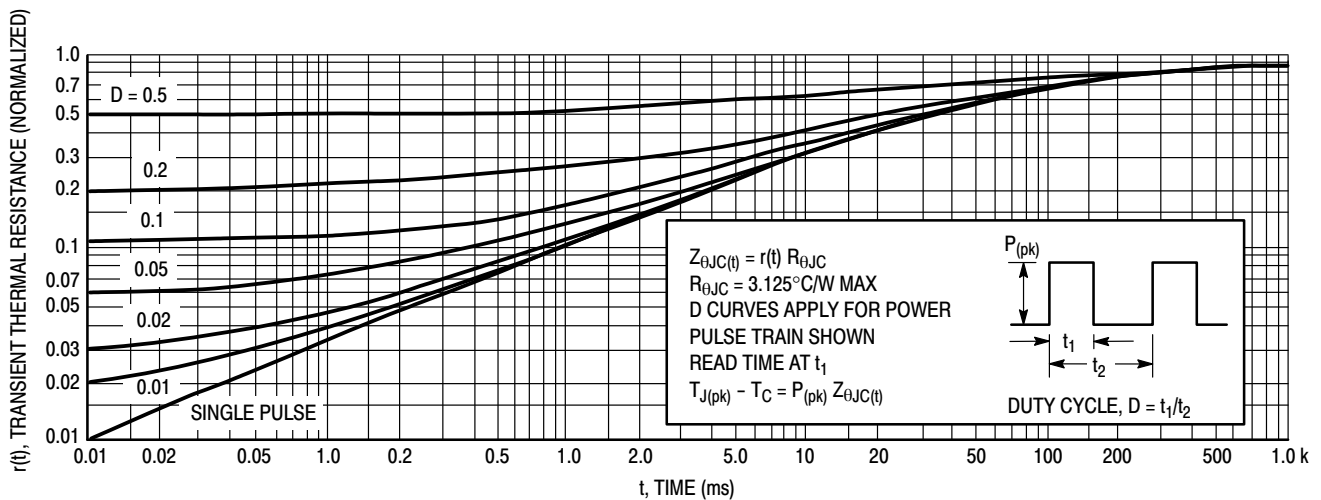


Figure 4. Thermal Response

TIP47G, TIP48G, TIP50G

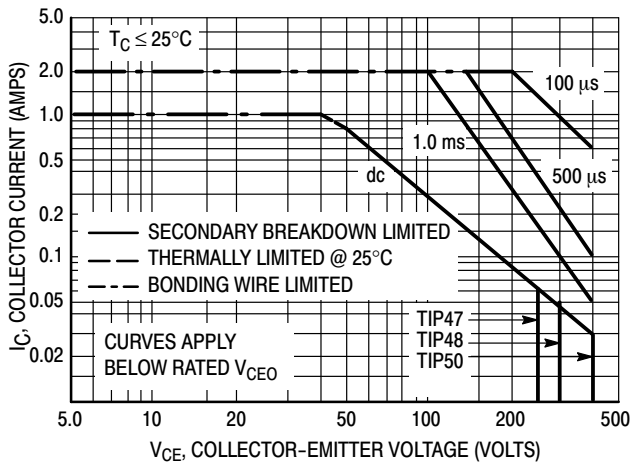


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

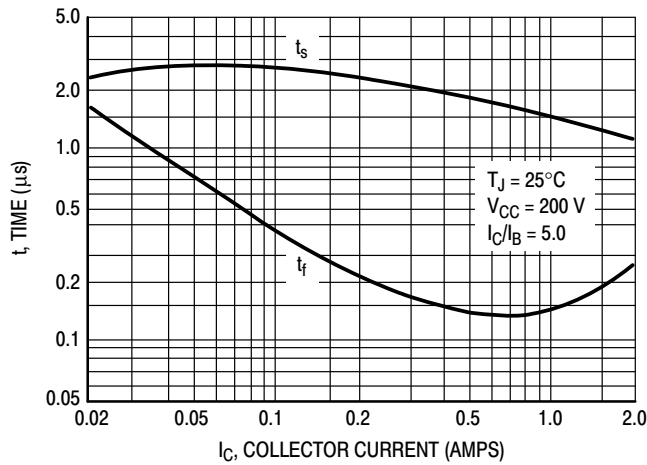


Figure 6. Turn-Off Time

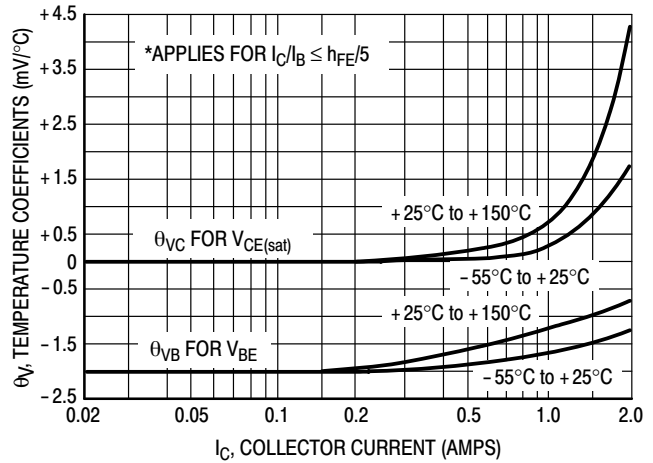
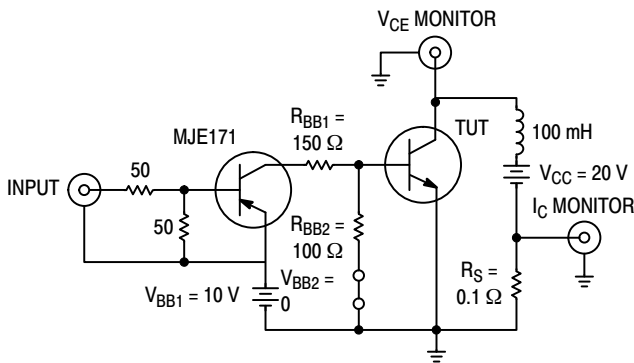


Figure 7. Temperature Coefficients



Note A: Input pulse width is increased until $I_{CM} = 0.63\text{ A}$.

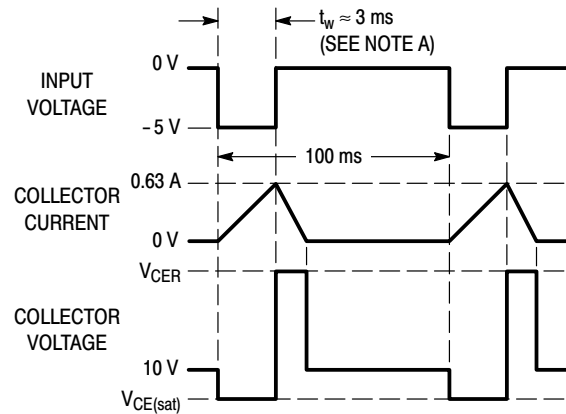


Figure 8. Inductive Load Switching

TIP47G, TIP48G, TIP50G

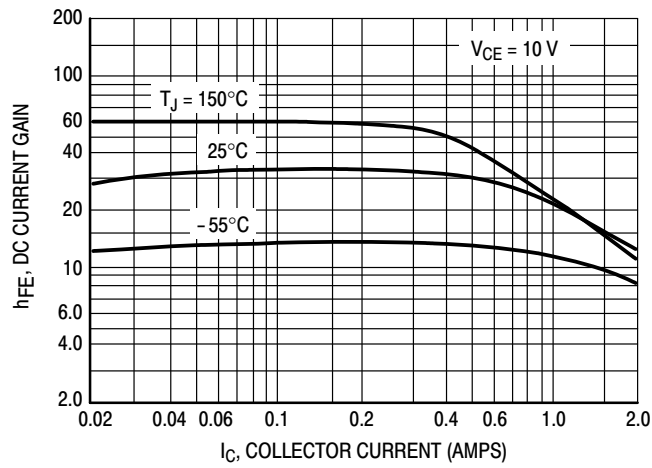


Figure 9. DC Current Gain

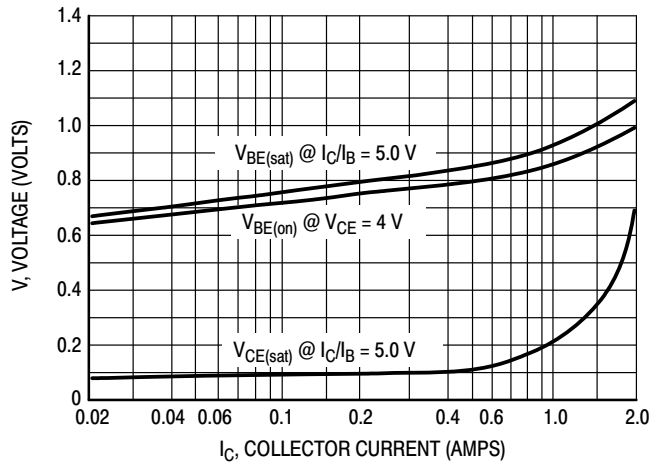
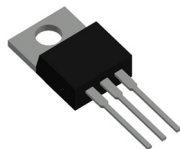


Figure 10. "On" Voltages

ORDERING INFORMATION

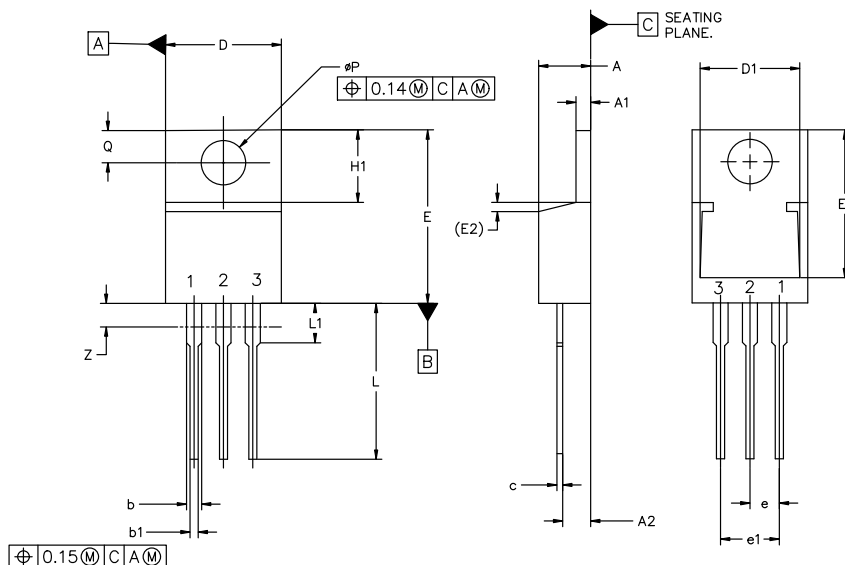
Device	Package	Shipping
TIP47G	TO-220 (Pb-Free)	50 Units / Rail
TIP48G	TO-220 (Pb-Free)	50 Units / Rail
TIP49G	TO-220 (Pb-Free)	50 Units / Rail
TIP50G	TO-220 (Pb-Free)	50 Units / Rail



TO-220-3 10.10x15.12x4.45, 2.54P

CASE 221A
ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
φP	3.60	3.85	4.09
Z	---	---	3.48

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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		PAGE 1 OF 1

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